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Title: Structural Characterization of the Interface Structure of Amorphous Silicon Thin Films after Post-deposition Argon or Hydrogen Plasma Treatment

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Highlights

- 1. Post-deposition argon plasma treatment for interface passivation is proposed
- 2. Proposed method leads to overall superior material properties
- 3. Microstructure and tail width is affected by the plasma treatment
- 4. Effect is still considerable for thick a-Si:H layers
- 5. Material restructuration explains fully the beneficial influence

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